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TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSIII)

2SK2845

Chopper Regulator, DC–DC Converter and Motor Drive Applications

- Low drain-source ON resistance $: RDS (ON) = 8.0 \Omega (typ.)$
- High forward transfer admittance $: |Y_{fs}| = 0.9 \text{ S (typ.)}$
- Low leakage current $: IDSS = 100 \mu A (max) (VDS = 720 V)$
- Enhancement mode : $V_{th} = 2.0 \sim 4.0 V (V_{DS} = 10 V, I_D = 1 mA)$

Maximum Ratings (Ta = 25°C)

Characteri	stics	Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	900	V	
Drain-gate voltage (R _{GS} = 20 kΩ)		V _{DGR}	900	V	
Gate-source voltage		V _{GSS}	±30	V	
Drain current	DC (Note 1)	۱ _D	1	A	
	Pulse (Note 1)	I _{DP}	3		
Drain power dissipatio	n (Tc = 25°C)	PD	40	W	
Single pulse avalanche energy (Note 2)		E _{AS}	324	mJ	
Avalanche current		I _{AR}	1	A	
Repetitive avalanche energy (Note 3)		E _{AR}	4.0	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

Thermal Characteristics

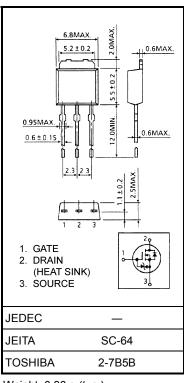
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	3.125	°C / W
Thermal resistance, channel to ambient	R _{th (ch−a)}	125	°C / W

Note 1: Ensure that the channel temperature does not exceed 150°C.

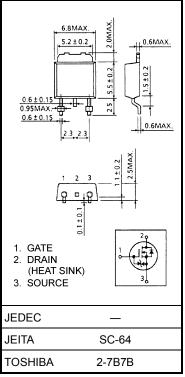
Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 594 mH, R_G = 25 Ω , I_{AR} = 1 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.



Weight: 0.36 g (typ.)



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Unit: mm

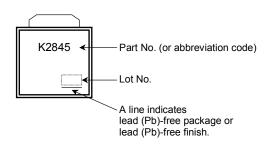
Electrical Characteristics (Ta = 25°C)

Charao	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	urrent	I _{GSS}	V _{GS} = ±30 V, V _{DS} = 0 V		—	±10	μA
Gate-source br	eakdown voltage	V (BR) GSS	I _G = ±10 μA, V _{DS} = 0 V	±30	_	_	V
Drain cut-off cu	rrent	I _{DSS}	V _{DS} = 720 V, V _{GS} = 0 V		_	100	μA
Drain-source br voltage	eakdown	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	900	_	_	V
Gate threshold	voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	2.0	_	4.0	V
Drain-source O	N resistance	R _{DS (ON)}	V _{GS} = 10 V, I _D = 0.5 A	_	8.0	9.0	Ω
Forward transfe	r admittance	Y _{fs}	V _{DS} = 20 V, I _D = 0.5 A	0.45	0.9	_	S
Input capacitant	ce	C _{iss}			350		
Reverse transfer capacitance		C _{rss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz		8	_	pF
Output capacitance		C _{oss}			40	—	
Switching time	Rise time	tr	$V_{GS} \stackrel{10V}{}_{0V} \prod_{OV\\ OV\\ C \\ C$	_	20	_	
	Turn-on time	t _{on}		_	70	_	20
	Fall time	t _f		_	30	_	ns
	Turn-off time	t _{off}	Duty $\leq 1\%$, t _w =10 μ s	_	95	_	
Total gate charge (gate-source plus gate-drain)		Qg		_	15	—	
Gate-source charge		Q _{gs}	V _{DD} ≈ 400 V, V _{GS} = 10 V, I _D = 1 A		6	_	nC
Gate-drain ("miller") Charge		Q _{gd}			9	_	

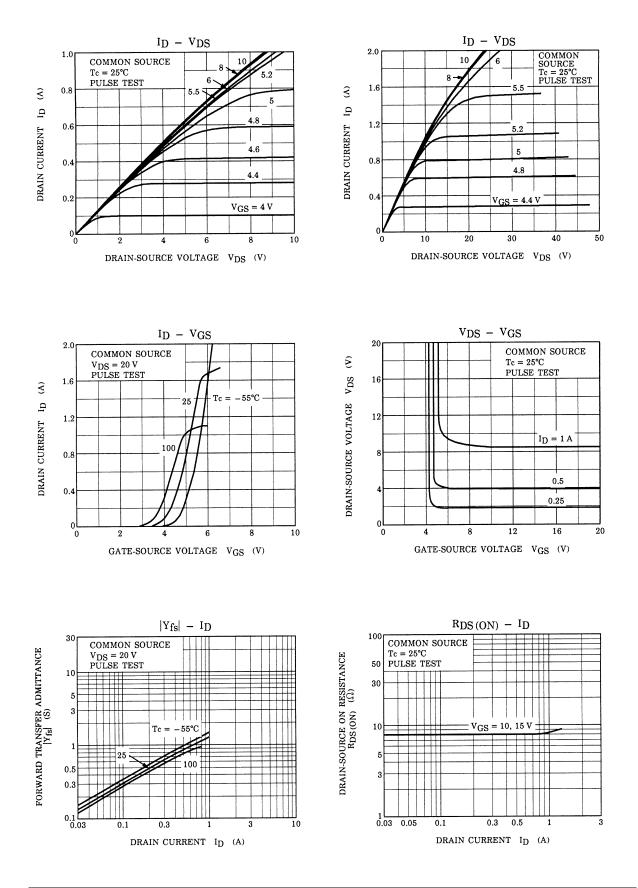
Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	_	_	1	А
Pulse drain reverse current (Note 1)	I _{DRP}	—	_	_	3	А
Forward voltage (diode)	V _{DSF}	I _{DR} = 1 A, V _{GS} = 0 V	_	_	-1.9	V
Reverse recovery time	t _{rr}	I _{DR} = 1 A, V _{GS} = 0 VdI _{DR} / dt = 100 A / μs	—	750	—	ns
Reverse recovery charge	Q _{rr}		-	3	-	μC

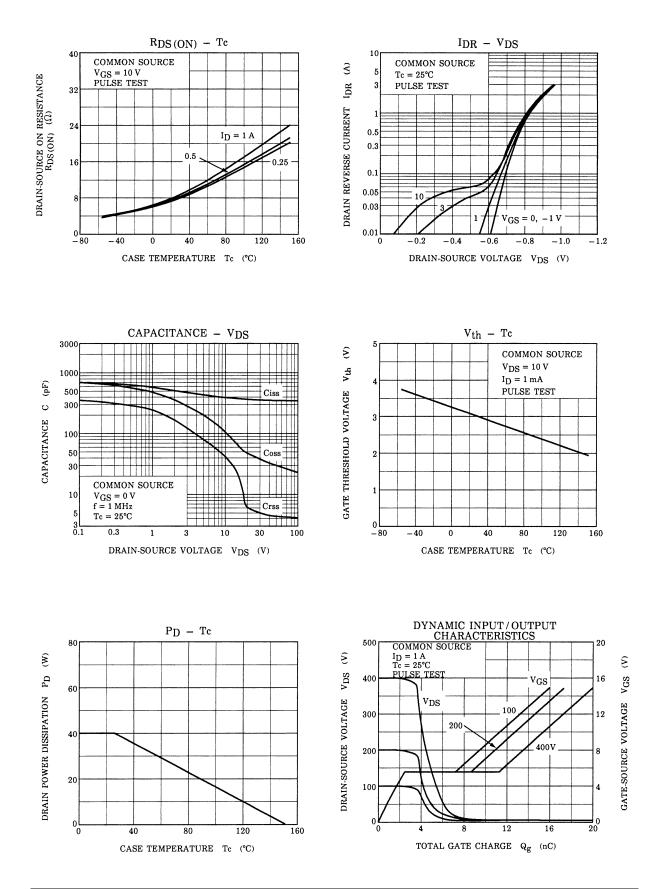
Marking

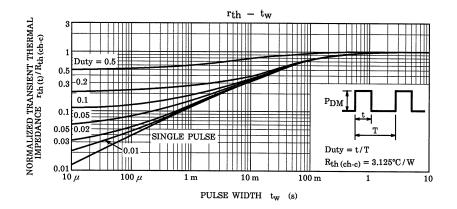


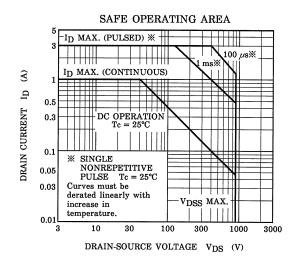
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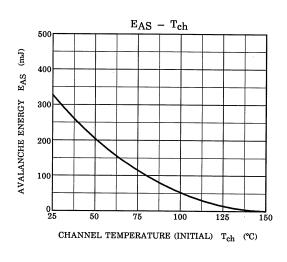


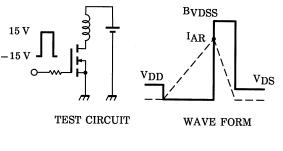
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$$\begin{array}{l} \mathrm{RG} = 25 \; \Omega \\ \mathrm{VDD} = 90 \; \mathrm{V}, \; \mathrm{L} = 594 \; \mathrm{mH} \end{array} \qquad \qquad \mathrm{EAS} = \frac{1}{2} \cdot \mathrm{L} \cdot \mathrm{I}^2 \cdot \left(\frac{\mathrm{B} \mathrm{VDSS}}{\mathrm{B} \mathrm{VDSS} - \mathrm{VDD}} \right) \\ \end{array}$$

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